

Part Number: IB0810M210



L-Band Radar Transistor

The high power pulsed radar transistor device part number IB0810M210 is designed for L-Band radar systems operating over the instantaneous bandwidth of 870-990 MHz. While operating in class C mode this common base device supplies a minimum of 210 watts of peak pulse power under the conditions of 300μs pulse width and 15% duty cycle. All devices are 100% screened for large signal RF parameters in a broadband RF test fixture with no external tuning. Excellent spectral stability into output mismatch over a broad input power range make it ideal for use in reliable high power solid state transmitters.



Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Unmatched Thermal Reliability

RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

FREQ (MHz)	Pout (W)	1 dB-OD-Pout (W)	Pin (W)	Ic (A)	IRL (dB)	Droop (dB)	Gain (dB)	Nc (%)	Δ Gain (dB)	VSWR 2:1	VSWR 3:1
870	210	239	31.6	9.907	17	-0.12	8.2	59	0.19	S	P
930	210	244	32.1	9.887	16.0	-0.01	8.2	59		S	P
990	210	246	30.7	9.280	16.0	-0.10	8.4	63		S	P

Part Number: **IB0810M210****Integra**
TECHNOLOGIES, INC.**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	75	V	$V_{BE}=0V$.
BD	Emitter-Base Voltage	V_{EBO}	--	3.0	V	--
BD	Storage Temperature Range	T_{STG}	-65	+200	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.35	°C/W	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{OUT}=210W$.
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification.
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C.
BD	Fine leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition H.
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					
Note	Screen 'BD' = parameter qualified By Design.					

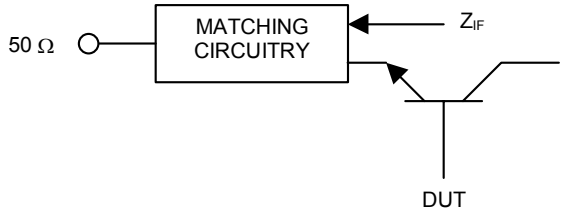
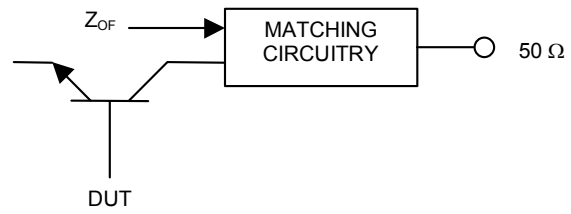
DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	75	--	V	$I_C=40mA, V_{BE}=0V, T_F=25\pm5^\circ C$.
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	20	mA	$V_{CE}=30V, V_{BE}=0V, T_F=25\pm5^\circ C$.
100%	DC Current Gain	H_{FE}	10	100	--	$V_{CE}=5V, I_C=0.1A, T_F=25\pm5^\circ C$.

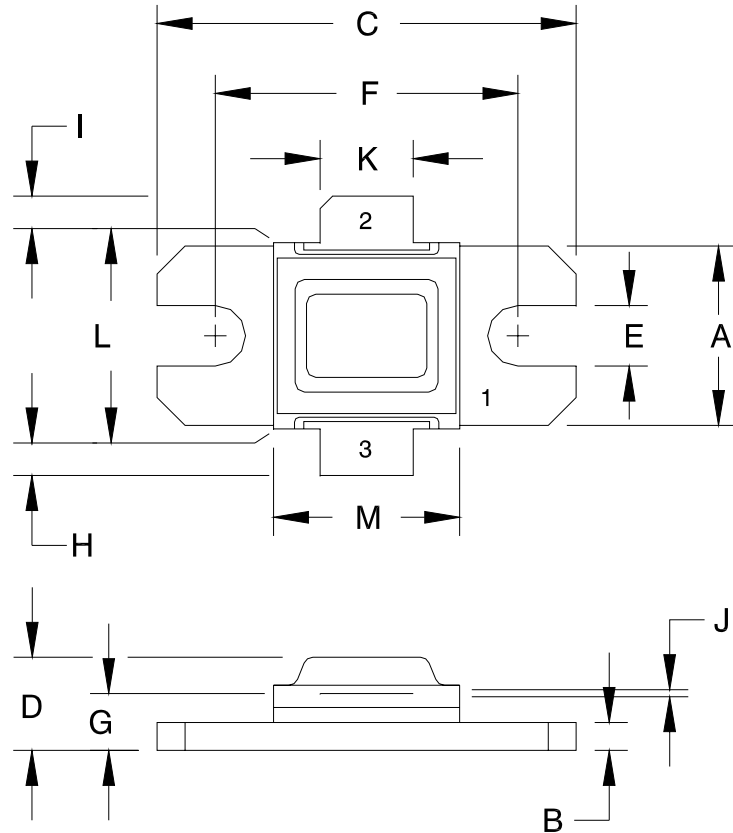
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	10	--	dB	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$.
100%	Output Power	P_{OUT}	210	--	W	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$.
100%	Collector Efficiency ($P_o/I_c/V_{CC}$)	N_c	50	--	%	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$.
100%	Power Gain	G	7.5	9.0	dB	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$.
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$. Delta peak power between 10 and 290us time positions.
100%	Power Gain Flatness versus Frequency	PGF	--	1.0	dB	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$. Calculate from $G_{MAX} - G_{MIN}$ @ $F=F1$, $F2$ & $F3$.
100%	Stability into 2:1 VSWR	VSWR-S	--	--	--	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$. Repeat P_o . Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse. All non-harmonically related signals must be at least -65 dBc.
100%	3:1 Load Mismatch Tolerance	LMT	--	--	--	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ\text{C}$, $P_{IN}=P_{IN1}$, $F=F1$, $F2$, $F3$. Repeat P_o . Rotate 3:1 output VSWR through 360° phase. Post-test $P_o = \text{Pre-test } P_o \pm 2.5W$.
Note	$V1 = 36V$; $PW1 = 300\mu\text{s}$; $DF1 = 15\%$; $P_{IN1} = 34W$; $F1 = 870 \text{ MHz}$, $F2 = 930 \text{ MHz}$, $F3 = 990 \text{ MHz}$.					
Note	$T_F = \text{Device flange temperature}$.					

BROADBAND RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
870	1.3 - j1.8	1.4 - j0.2
930	1.4 - j1.3	1.1 - j0.3
990	1.4 - j1.0	0.7 - j0.2
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.380	0.390	9.65	9.91
B	0.058	0.062	1.47	1.57
C	0.895	0.905	22.73	22.99
D	0.195	0.205	4.95	5.21
E	0.125	0.135	3.18	3.43
F	0.645	0.655	16.38	16.64
G	0.112	0.132	2.84	3.35
H	0.080	0.120	2.03	3.05
I	0.080	0.120	2.03	3.05
J	0.003	0.005	0.08	0.13
K	0.195	0.205	4.95	5.21
L	0.395	0.405	10.03	10.29
M	0.395	0.405	10.03	10.29

PIN	
1	BASE
2	COLLECTOR
3	EMITTER

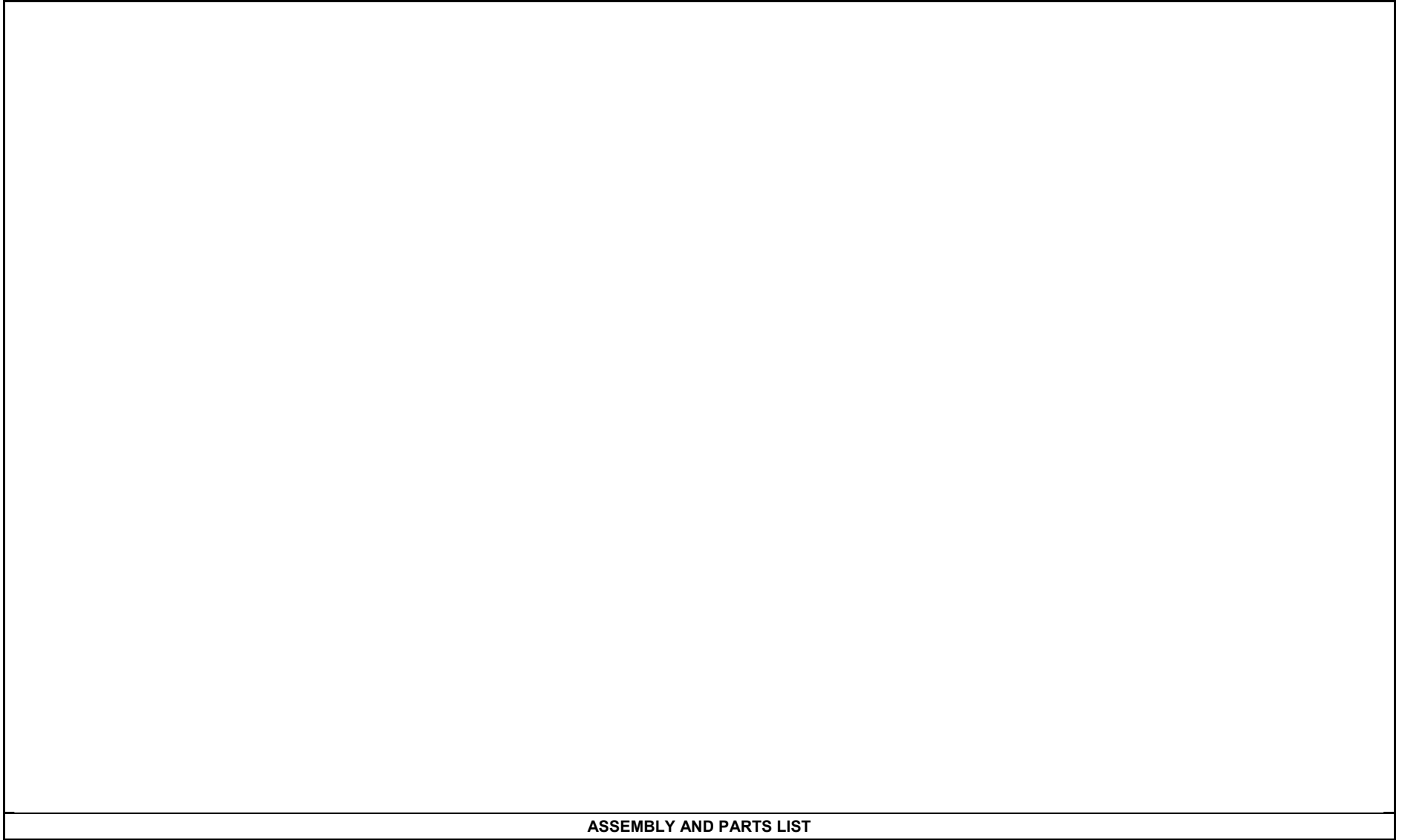
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DOCUMENT NUMBER: IB0810M210	REV: NC
SHEET NAME: 06-OUTLINE	REV: A

Part Number: **IB0810M210**

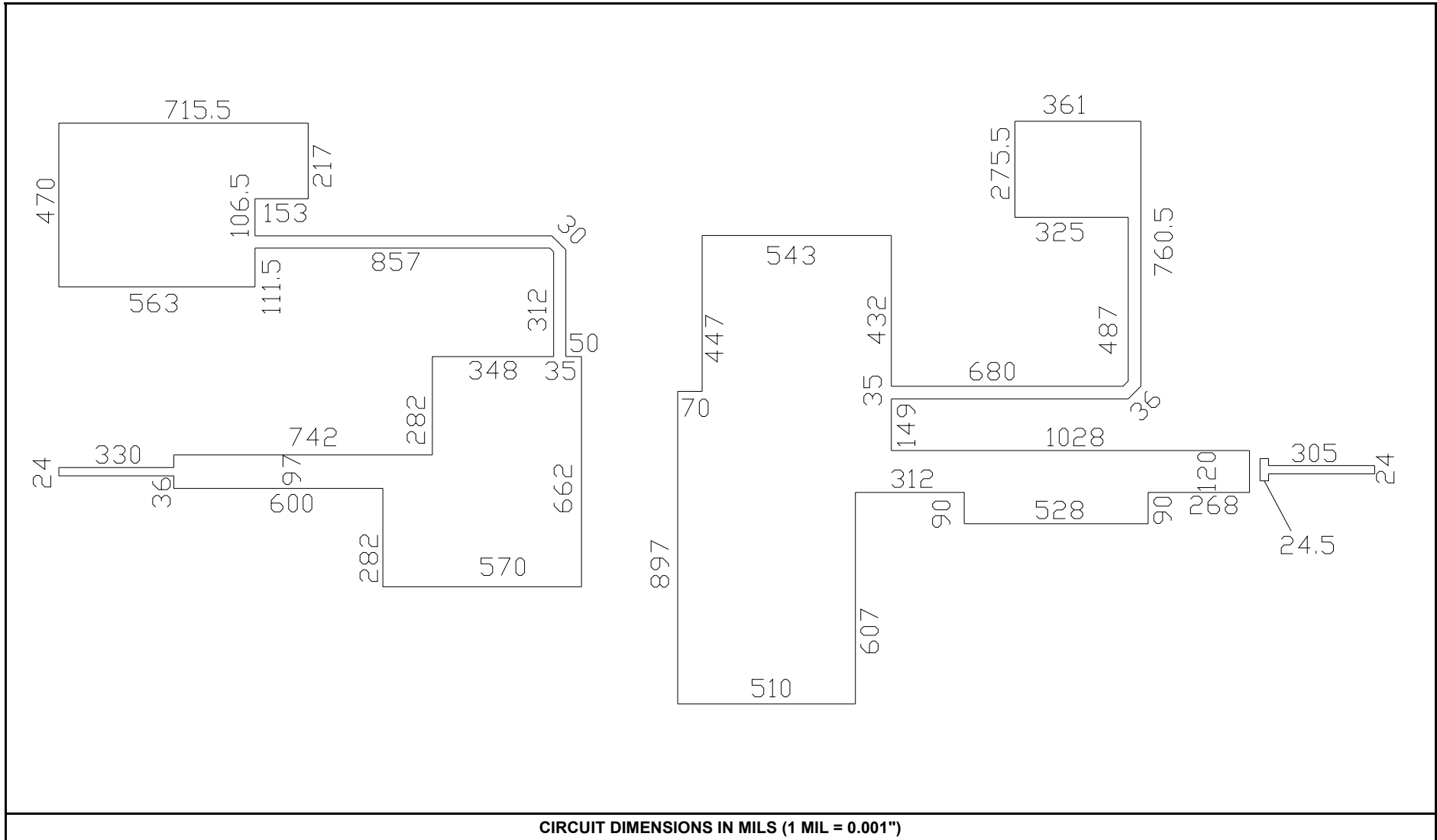
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BROADBAND RF TEST FIXTURE

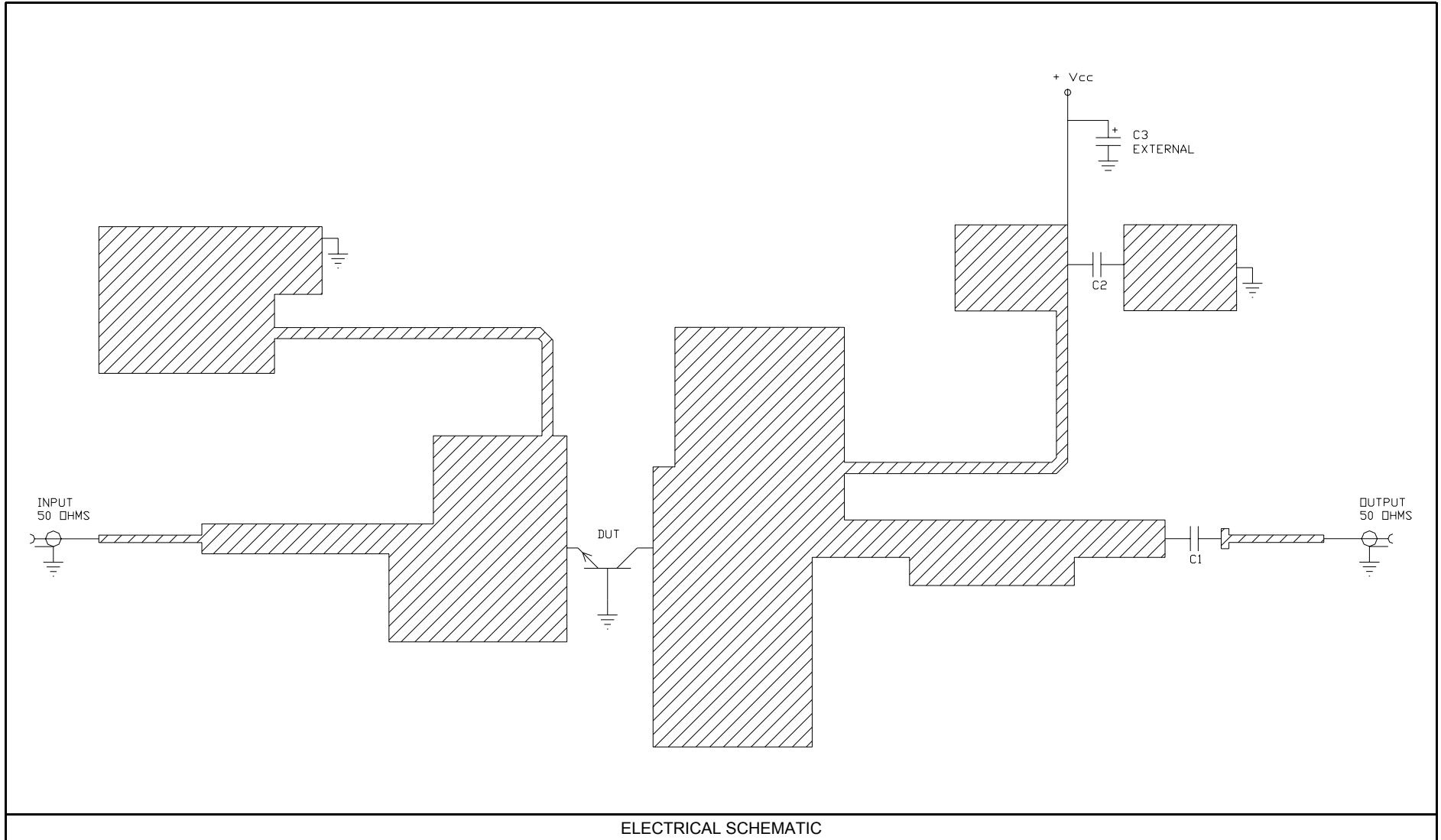


ASSEMBLY AND PARTS LIST

BROADBAND RF TEST FIXTURE



BROADBAND RF TEST FIXTURE



ELECTRICAL SCHEMATIC

Part Number: **IB0810M210****Integra**
TECHNOLOGIES, INC.**DEFINITIONS**

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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